

Vishay Semiconductors

# Ultrafast Rectifier, 10 A FRED Pt®



TO.	220	AD

Base common cathode 2						
Anode 0	Com	) 2 Imon Iode	<b>▲</b> ○ A 3	node		

PRODUCT SUMMARY					
Package	TO-220AB				
I <sub>F(AV)</sub>	2 x 5 A				
$V_{R}$	200 V				
V <sub>F</sub> at I <sub>F</sub>	0.87 V				
t <sub>rr</sub> typ.	See Recovery table				
T <sub>J</sub> max.	175 °C				
Diode variation	Common cathode				

#### **FEATURES**

- Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS
COMPLIANT
HALOGEN
FREE

### **DESCRIPTION / APPLICATIONS**

VS-MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Peak repetitive reverse voltage	$V_{RRM}$		200	V				
Average rectified forward current	leg		5					
Average rectified forward current total dev	vice I <sub>F(AV)</sub>	Rated V <sub>R</sub> , T <sub>C</sub> = 149 °C	10					
Non-repetitive peak surge current per leg	I <sub>FSM</sub>		50	Α				
Peak repetitive forward current per leg	I <sub>FM</sub>	Rated $V_R$ , square wave, 20 kHz $T_C = 149  ^{\circ}C$	10					
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C				

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	200	-	-		
Forward voltage V <sub>F</sub>		I <sub>F</sub> = 5 A, T <sub>J</sub> = 125 °C	-	0.87	0.99	V	
	V <sub>F</sub>	I <sub>F</sub> = 10 A, T <sub>J</sub> = 125 °C	-	1.02	1.20		
		I <sub>F</sub> = 10 A	-	1.12	1.25		
Payaraa laakaga aurrant		V <sub>R</sub> = V <sub>R</sub> rated	-	-	10		
Reverse leakage current I <sub>R</sub>		T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	-	250	- μΑ	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	8	-	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	=	8.0	-	nH	



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, dI_F/dt =$	$50 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	-	-	35		
Payaraa raaayan, tima		$I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A}, I_{REC} = 0.25 \text{ A}$		-	-	25	ns	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 5 A dI <sub>F</sub> /dt = 200 A/μs	-	24	-	115	
		T <sub>J</sub> = 125 °C			-	35	-	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	3.3	-	۸	
		T <sub>J</sub> = 125 °C	$V_{\rm R} = 160 \text{ V}$	-	5.0	-	A	
Reverse recovery charge	0	T <sub>J</sub> = 25 °C	-n3 •	-	33	-	nC	
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	76	-	110	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C	
Thermal resistance, junction to case per leg	R <sub>thJC</sub>		-	-	5		
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>		-	-	50	°C/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-		
Weight			-	2.0	-	g	
vveigni			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AB		MUR1	020CT		

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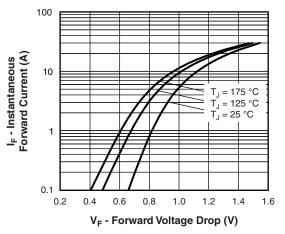


Fig. 1 - Typical Forward Voltage Drop Characteristics

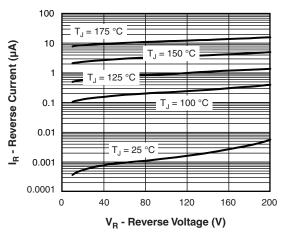


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

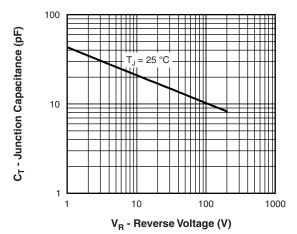


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

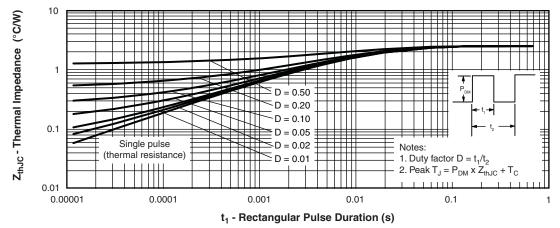
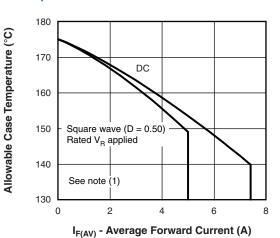


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

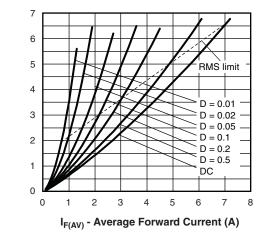


Fig. 6 - Forward Power Loss Characteristics

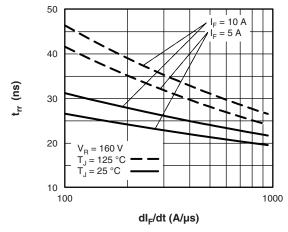


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

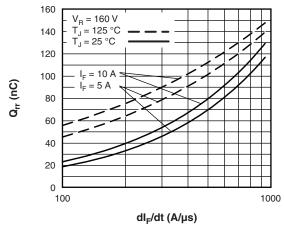


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

Average Power Loss (W)

 $^{(1)}$  Formula used:  $T_{C} = T_{J}$  - (Pd + Pd\_{REV}) x  $R_{thJC};$  $Pd = Forward\ power\ loss = I_{F(AV)}\ x\ V_{FM}\ at\ (I_{F(AV)}/D)\ (see\ fig.\ 6);$   $Pd_{REV} = Inverse\ power\ loss = V_{R1}\ x\ I_R\ (1\ -\ D);\ I_R\ at\ V_{R1} = Rated\ V_R$ 

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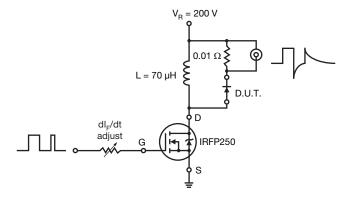
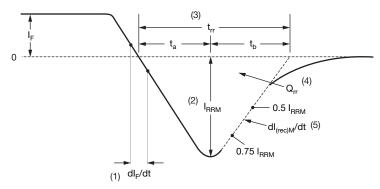


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

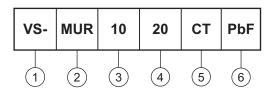
(5) dl<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 10 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Ultrafast MUR series

Current rating (10 = 10 A)

Voltage rating (20 = 200 V)

- CT = center tap (dual) TO-220/D<sup>2</sup>PAK/TO-262

6 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-MUR1020CTPbF	50	1000	Antistatic plastic tube				
VS-MUR1020CT-N3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95222</u>					
Dout moulding information	TO-220ABPbF	www.vishay.com/doc?95225			
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028			



### Vishay Semiconductors

### **TO-220AB**

#### **DIMENSIONS** in millimeters and inches



### Lead assignments

#### **Diodes**

- 1. Anode/open
- 2. Cathode
- 3. Anode

#### Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIMETERS INCHES		NOTES		
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° t	o 93°	
		•	•	•	

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip



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